



IRFB4110PBF Information

Part Number IRFB4110PBF

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 100V 120A TO-220AB

TO-220-3 **Package**

For the pricing/inventory/lead time, please contact

Website: https://www.heisener.com For Reference Only

E-mail: salesdept@heisener.com



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IRFB4110PBF Specifications

| Manufacturer Part NumberIRFB4110PBFManufacturerInfineon TechnologiesCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-220-3SeriesHEXFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C120A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vgs210nC @ 10VInput Capacitance (Ciss) (Max) @ Vds9620pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)370W (Tc)Rds On (Max) @ Id, Vgs4.5 mOhm @ 75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3Report errors? | | |
|---|--|--------------------------------------|
| Category Discrete Semiconductor Products Package TO-220-3 Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 120A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 210nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 9620pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 370W (Tc) Rds On (Max) @ Id, Vgs 4.5 mOhm @ 75A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3 | Manufacturer Part Number | IRFB4110PBF |
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| FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C120A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs210nC @ 10VInput Capacitance (Ciss) (Max) @ Vds9620pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)370W (Tc)Rds On (Max) @ Id, Vgs4.5 mOhm @ 75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3 | Package | TO-220-3 |
| TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C120A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs210nC @ 10VInput Capacitance (Ciss) (Max) @ Vds9620pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)370W (Tc)Rds On (Max) @ Id, Vgs4.5 mOhm @ 75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3 | Series | HEXFET? |
| Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C120A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs210nC @ 10VInput Capacitance (Ciss) (Max) @ Vds9620pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)370W (Tc)Rds On (Max) @ Id, Vgs4.5 mOhm @ 75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3 | FET Type | N-Channel |
| Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.5 mOhm @ 75A, 10V Operating Temperature Supplier Device Package Package / Case 120A (Tc) 120A (Tc) | Technology | MOSFET (Metal Oxide) |
| Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 210nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.5 mOhm @ 75A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-220AB | Drain to Source Voltage (Vdss) | 100V |
| Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 4V @ 250μA 210nC @ 10V 4.5 mOhr @ 750V 4.5 mOhr @ 75A, 10V 75°C ~ 175°C (TJ) Through Hole TO-220AB TO-220AB | Current - Continuous Drain (Id) @ 25°C | 120A (Tc) |
| Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 9620pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.5 mOhm @ 75A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-220AB TO-220-3 | Drive Voltage (Max Rds On, Min Rds On) | 10V |
| Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.5 mOhm @ 75A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3 | Vgs(th) (Max) @ Id | 4V @ 250μA |
| Vgs (Max)±20VFET Feature-Power Dissipation (Max)370W (Tc)Rds On (Max) @ Id, Vgs4.5 mOhm @ 75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3 | Gate Charge (Qg) (Max) @ Vgs | 210nC @ 10V |
| FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.5 mOhm @ 75A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-220AB TO-220-3 | Input Capacitance (Ciss) (Max) @ Vds | 9620pF @ 50V |
| Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.5 mOhm @ 75A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3 | Vgs (Max) | ±20V |
| Rds On (Max) @ Id, Vgs4.5 mOhm @ 75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3 | FET Feature | - |
| Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3 | Power Dissipation (Max) | 370W (Tc) |
| Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3 | Rds On (Max) @ Id, Vgs | 4.5 mOhm @ 75A, 10V |
| Supplier Device Package TO-220AB Package / Case TO-220-3 | Operating Temperature | -55°C ~ 175°C (TJ) |
| Package / Case TO-220-3 | Mounting Type | Through Hole |
| | Supplier Device Package | TO-220AB |
| Report errors? | Package / Case | TO-220-3 |
| | | Report errors? |

IRFB4110PBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRFB4110PBF Payment Methods



















IRFB4110PBF Shipping Methods













If you have any question about IRFB4110PBF, please do not hesitate to contact us!

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